

In the Specification:

Please substitute the following paragraphs for the corresponding paragraphs beginning at the indicated location in the specification as originally filed.

(Page 15, lines 15+)

Then, as shown in Figure 14, a resist is applied, exposed, developed and thus patterned to cover only one of spacers 1302. Registration may be somewhat critical for devices of small minimum feature size but it should be appreciated that the process window for exposure and registration of the mask edge is only slightly smaller than the minimum feature size and thus necessarily within the capacity of the exposure tool capable of other processes at similar resolution. One of spacers 1302 is thus removed by selectively etching while the other is protected by the resist, as shown in Figure 15; after which dopant can be outdiffused from the remaining spacer solid body to form impurity structure 1502.